TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ($L^2$-$\pi$-MOSV)

# 2SK2201

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS

- 4 V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS\,(ON)} = 0.28\ \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 3.5$ S (Typ.)
- Low Leakage Current : $I_{DSS} = 100\ \mu$A (Max.) ($V_{DS} = 100$ V)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0$ V ($V_{DS} = 10$ V, $I_D = 1$ mA)

MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | 100 | V |
| Drain-Gate Voltage ($R_{GS} = 20\ k\Omega$) | | $V_{DGR}$ | 100 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±20 | V |
| Drain Current | DC | $I_D$ | 3 | A |
| | Pulse | $I_{DP}$ | 12 | A |
| Drain Power Dissipation (Tc = 25°C) | | $P_D$ | 20 | W |
| Single Pulse Avalanche Energy** | | $E_{AS}$ | 140 | mJ |
| Avalanche Current | | $I_{AR}$ | 3 | A |
| Repetitive Avalanche Energy* | | $E_{AR}$ | 2 | mJ |
| Channel Temperature | | $T_{ch}$ | 150 | °C |
| Storage Temperature Range | | $T_{stg}$ | −55~150 | °C |

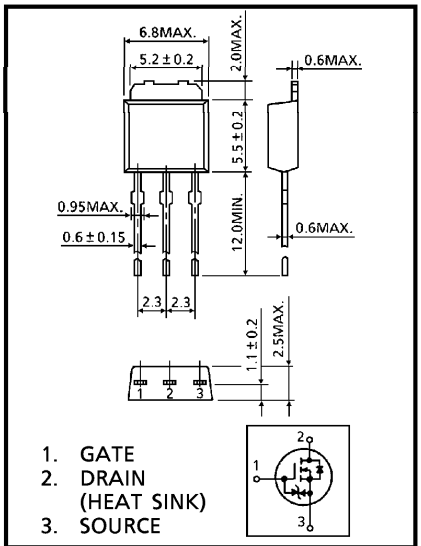
THERMAL CHARACTERISTICS

| CHARACTERISTIC | SYMBOL | MAX. | UNIT |
|---|---|---|---|
| Thermal Resistance, Channel To Case | $R_{th\,(ch\text{-}c)}$ | 6.25 | °C / W |
| Thermal Resistance, Channel To Ambient | $R_{th\,(ch\text{-}a)}$ | 125 | °C / W |

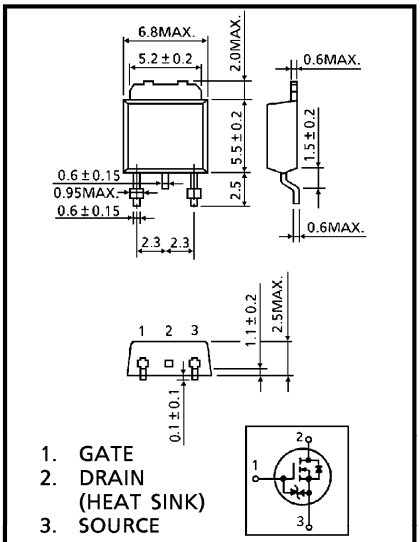
Note ;
* Repetitive rating ; Pulse Width Limited by Max. junction temperature.
** $V_{DD} = 50$ V, $T_{ch} = 25$°C (initial), L = 25 mH, $R_G = 25\ \Omega$, $I_{AR} = 3$ A

**This transistor is an electrostatic sensitive device. Please handle with caution.**

Unit in mm




| | |
|---|---|
| JEDEC | — |
| EIAJ | SC-64 |
| TOSHIBA | 2-7B1B |




| | |
|---|---|
| JEDEC | — |
| EIAJ | SC-64 |
| TOSHIBA | 2-7B2B |

Weight : 0.36 g

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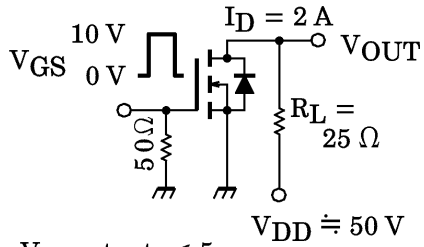
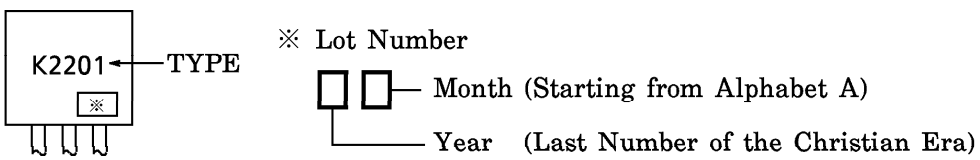
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|---|
| Gate Leakage Current | | $I_{GSS}$ | $V_{GS}$ = ±16 V, $V_{DS}$ = 0 V | — | — | ±10 | μA |
| Drain Cut-off Current | | $I_{DSS}$ | $V_{DS}$ = 100 V, $V_{GS}$ = 0 V | — | — | 100 | μA |
| Drain-Source Breakdown Voltage | | $V_{(BR)\,DSS}$ | $I_D$ = 10 mA, $V_{GS}$ = 0 V | 100 | — | — | V |
| Gate Threshold Voltage | | $V_{th}$ | $V_{DS}$ = 10 V, $I_D$ = 1 mA | 0.8 | — | 2.0 | V |
| Drain-Source ON Resistance | | $R_{DS\,(ON)}$ | $V_{GS}$ = 4 V, $I_D$ = 2 A | — | 0.36 | 0.45 | Ω |
| | | | $V_{GS}$ = 10 V, $I_D$ = 2 A | — | 0.28 | 0.35 | |
| Forward Transfer Admittance | | $\|Y_{fs}\|$ | $V_{DS}$ = 10 V, $I_D$ = 2 A | 1.5 | 3.5 | — | S |
| Input Capacitance | | $C_{iss}$ | $V_{DS}$ = 10 V, $V_{GS}$ = 0 V<br>f = 1 MHz | — | 280 | — | pF |
| Reverse Transfer Capacitance | | $C_{rss}$ | | — | 50 | — | |
| Output Capacitance | | $C_{oss}$ | | — | 105 | — | |
| Switching Time | Rise Time | $t_r$ |  <br>$V_{IN}$ : $t_r$, $t_f$ < 5 ns,<br>Duty ≦ 1%, $t_w$ = 10 μs | — | 20 | — | ns |
| | Turn-on Time | $t_{on}$ | | — | 50 | — | |
| | Fall Time | $t_f$ | | — | 40 | — | |
| | Turn-off Time | $t_{off}$ | | — | 170 | — | |
| Total Gate Charge (Gate-Source Plus Gate-Drain) | | $Q_g$ | $V_{DD}$ ≒ 80 V, $V_{GS}$ = 10 V<br>$I_D$ = 3 A | — | 13.5 | — | nC |
| Gate-Source Charge | | $Q_{gs}$ | | — | 8.5 | — | |
| Gate-Drain ("Miller") Charge | | $Q_{gd}$ | | — | 5 | — | |

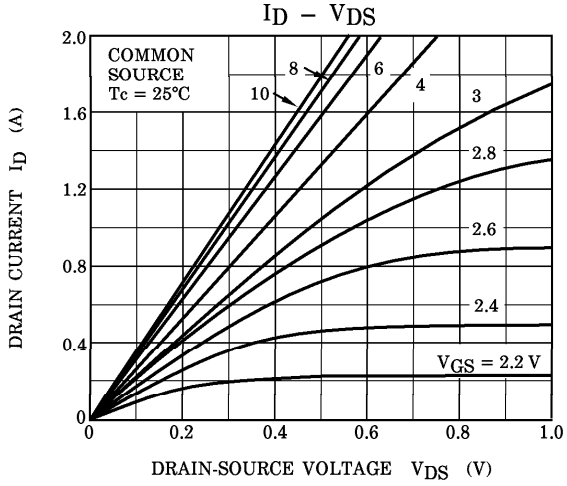
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| Continuous Drain Reverse Current | $I_{DR}$ | — | — | — | 3 | A |
| Pulse Drain Reverse Current | $I_{DRP}$ | — | — | — | 12 | A |
| Diode Forward Voltage | $V_{DSF}$ | $I_{DR}$ = 3 A, $V_{GS}$ = 0 V | — | — | −1.5 | V |
| Reverse Recovery Time | $t_{rr}$ | $I_{DR}$ = 3 A, $V_{GS}$ = 0 V<br>$dI_{DR}/dt$ = 50 A/μs | — | 100 | — | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | — | 0.2 | — | μC |

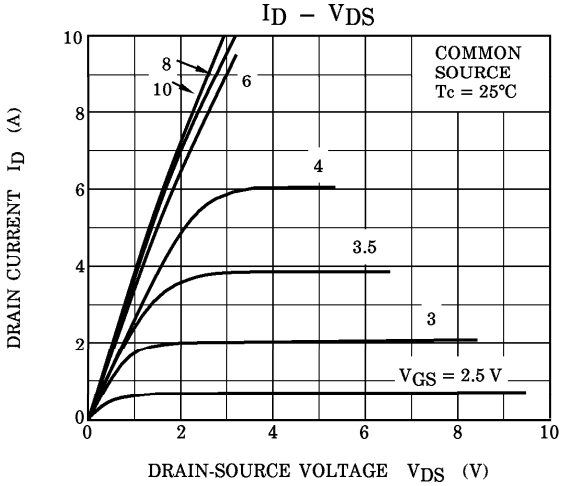
MARKING



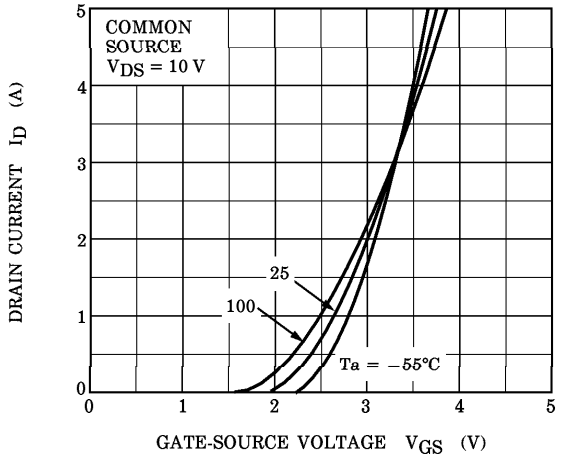
$I_D - V_{DS}$



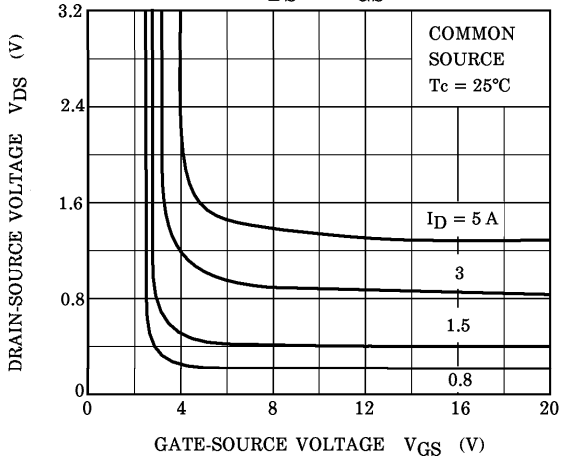

$I_D - V_{DS}$



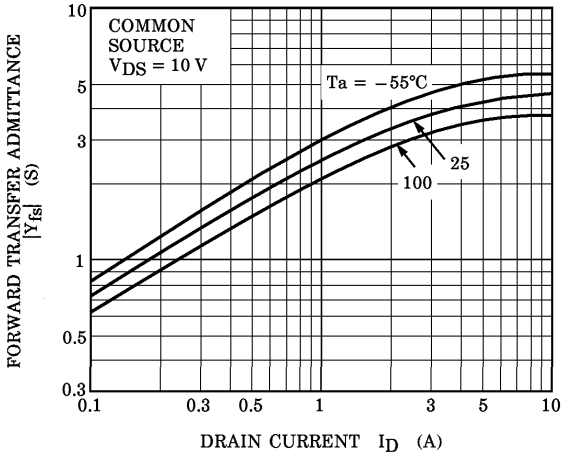

$I_D - V_{GS}$



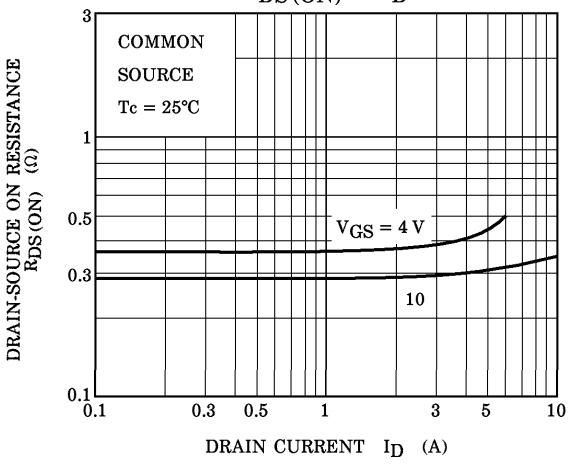

$V_{DS} - V_{GS}$



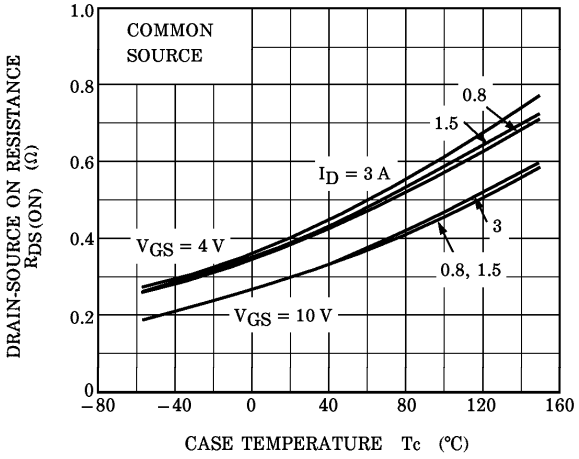

$|Y_{fs}| - I_D$



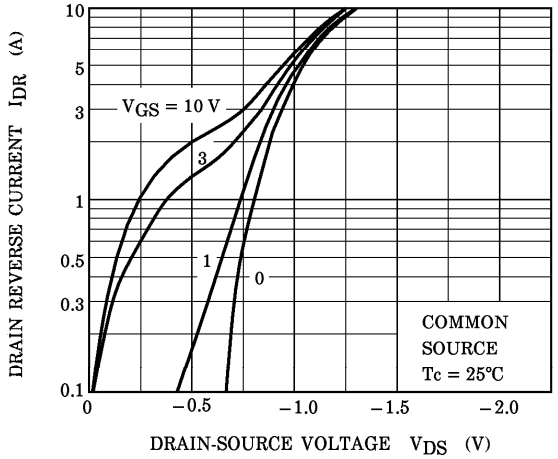

$R_{DS(ON)} - I_D$



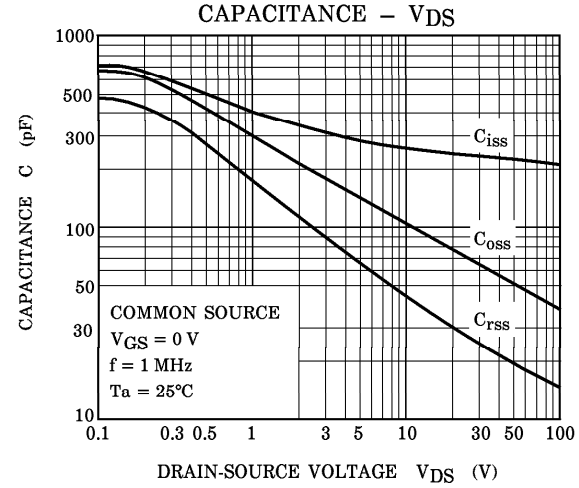
$R_{DS\,(ON)}$ – Tc



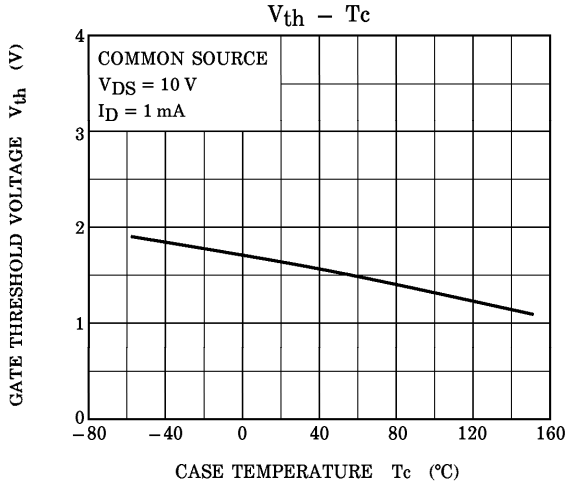

$I_{DR}$ – $V_{DS}$



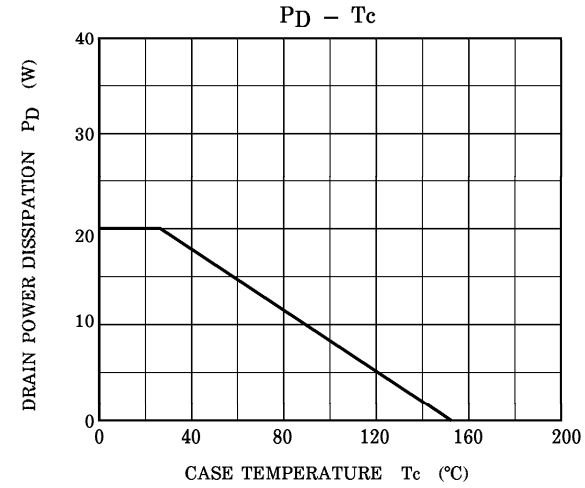

CAPACITANCE – $V_{DS}$



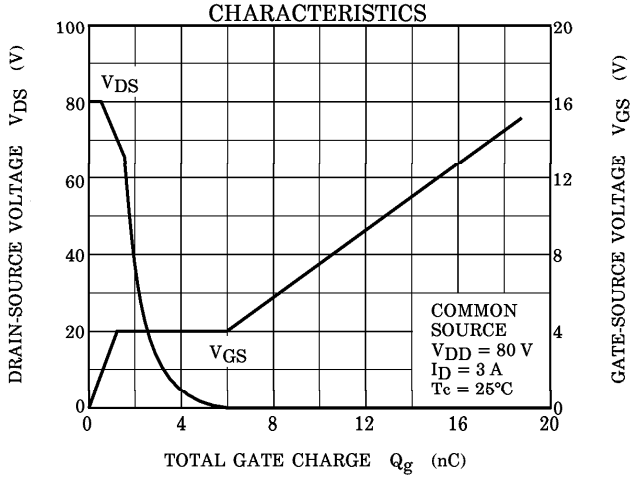

$V_{th}$ – Tc



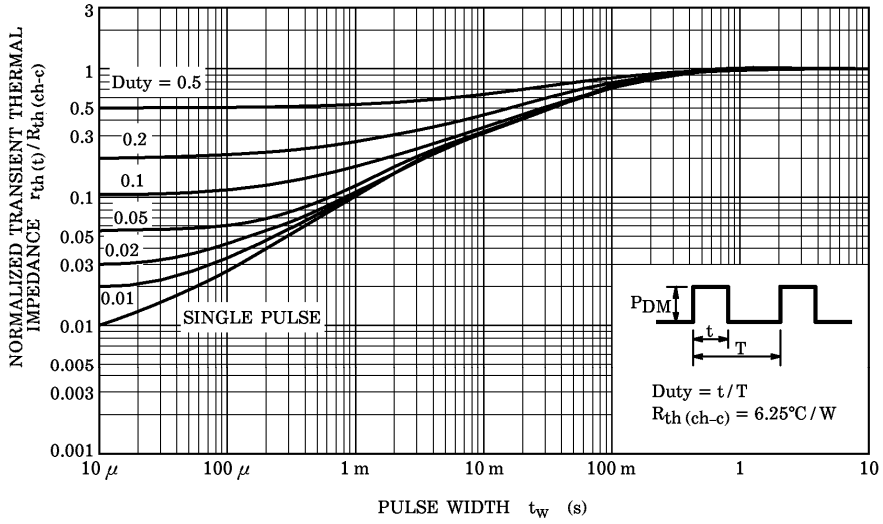

$P_D$ – Tc



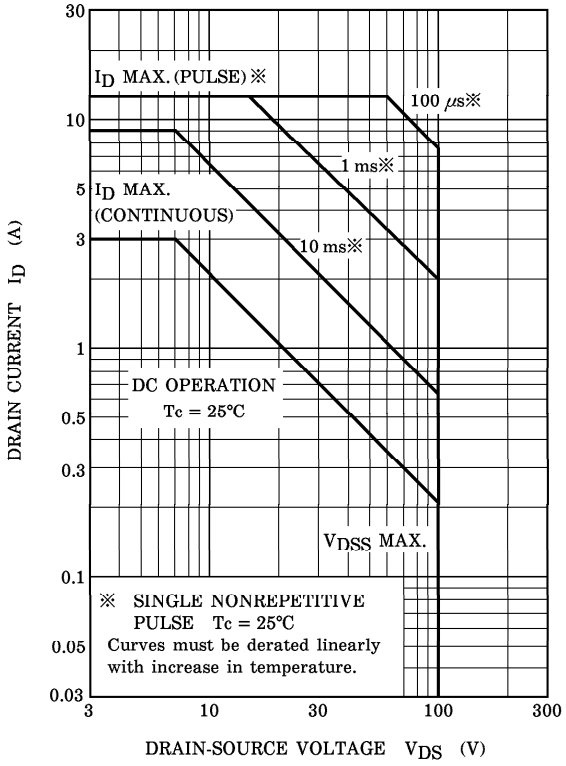

DYNAMIC INPUT / OUTPUT CHARACTERISTICS



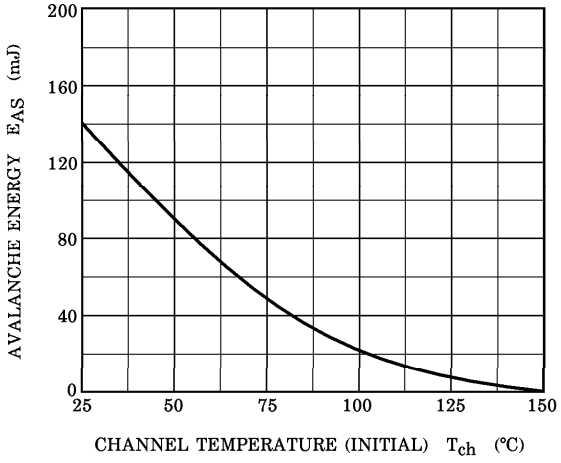
$r_{th}$ – $t_w$

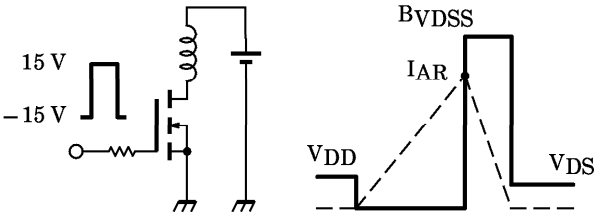



SAFE OPERATING AREA




$E_{AS}$ – $T_{ch}$




Peak $I_{AR}$ = 3 A, $R_G$ = 25 Ω
$V_{DD}$ = 25 V, L = 25 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$